A Giant Enhancement of Dielectric Permittivity in Highly Strained EuO

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Abstract

Recently, lattice dynamical properties of the highly strained europium monoxide, as a promising candidate for the strong ferroelectric-ferromagnet material, applied in the next generation storage devices, attracted a huge attention in the solid state electronic. Here, the authors investigate the effect of tensile strain on the dielectric properties of the PLD grown EuO thin films from 5 to 200 K. A nearly 3% out-of-plane lattice compression is observed as the film thickness decreases to 10 nm, which could originate from the lattice mismatch between film and substrate. The temperature and frequency dependence of the capacitance and loss factor of the films reveals the dominant role of the EuO electronic and ionic polarization below 100 K. The interdigitated capacitor fabricated on the strained film shows almost 50% increase of the capacitance compared to the relaxed one, which corresponds to a considerable enhancement of the dielectric permittivity (~ 9 times) induced by strain. Softening of the in-plane polarized transverse optical phonon modes of EuO lattice due to the tensile strain might have the major contribution to this behavior according to the Lyddane–Sachs–Teller relation.

Keywords: Dielectric properties; EuO; Pulsed laser deposition; Strained thin films; Lattice dynamics; Interdigitated electrodes; Phonon Softening; Lyddane–Sachs–Teller relation;

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Introduction

Of the most interesting approaches to generate new phenomena in materials, applying strain resulted in a group of physical system with a range of structural and electronic features, plays an crucial role in the development of the solid-state electronics [1–3]. Todays, the outstanding progress in the thin film industry in production and characterization as well enables scientists to produce highly strained materials and control the relaxation processes by using appropriate substrates. This development, in turn, caused the experimentally confirmation of the recent theoretical prediction and created emergent physical properties which have been hidden behind the bulk materials [4]. It was shown that a proper epitaxial strain adjusts electronic band structure [5], increases transition temperature in superconductors[6], ferromagnetic [7] and also ferroelectric [8–11] materials.

Among the various physical features, dielectric properties and lattice dynamics of materials, which are closely connected to the structural characteristics, are the most challenging subjects to be studied as a function of lattice strain. The progress in this field leads to a breakthrough in the development of 21st solid-state physics and an industrial revolution in energy-storage devices, renewable energy and memory devices.

Choi et al. showed that a biaxial compressive strain enhances the ferroelectric properties of BaTiO$_3$ thin films [9]. Their approach resulted in an increase of 350 °C in ferroelectric transition temperature and the remnant polarization was enhanced 250% higher than that of bulk one. Haeni et al. proved the emergent of ferroelectricity in the quantum para-electric SrTiO$_3$ by applying an appropriate strain [11]. According to their study the ferroelectric transition temperature arises to the room temperature in a nearly 1% epitaxially strained SrTiO$_3$ thin film grown on DyScO$_3$ substrates. Fennie and Rabe [12] with using first principle DFT calculation showed that with applying an appropriate strain a coupling between magnetic spins and ferroelectric ordering results in a strong multiferroics systems. It was confirmed experimentally by growing EuTiO$_3$ on different substrates to achieve a range of strained system [13]. Recently, the simplicity of the crystal and electronic structure of rocksalt binary oxides dragged theorist’s attention to investigate the dynamical properties of this group of materials under complex condition. Strain induced ferroelectricity [14–17], pressure induced Insulator-Metal transition [18,19], Magnetic alignment mechanisms [20], Spin-Phonon coupling at magnetic transition temperature [21] have been all predicted by first principle calculations on the binary oxides.

In a pioneering work, Bousquet et al. using first principles density functional calculations [15] and Bog G Kim [14] by applying soft mode group theory analysis, studied the effect of epitaxial strain on the lattice dynamics of rocksalt structure binary compounds. In their calculation, it was predicted that the epitaxial strain lowers the cubic symmetry of the system to the tetragonal and a critical strain causes the condensation of a particular phonon mode resulting in the break of inversion symmetry. A substantial softening of the zone center transverse optical (TO) phonon mode as the system is under tensile strain was predicted in their calculation which causes a huge increase of dielectric permittivity of the materials. Their approaches were applied to the magnetic binary oxides, GdN [16] and EuO [15] and surprisingly it was confirmed that under proper epitaxial strain both
oxides show ferroelectric transition in their preserved magnetic ground state. In a recent work, we showed that the low temperature dielectric constant of PLD grown strained NiO thin film shows the dielectric permittivity of almost two times higher than that of the bulk one [22]. Investigation of the effect of strain on the dielectric properties of EuO is much more thought-provoking as the bigger size of the Eu ion compared to Ni atom already provides a softer zone center TO phonon mode of about 199.3 cm\(^{-1}\) [23] related to the vibrations of Eu and O ions, which is much lower than that of Ni-O (384 cm\(^{-1}\)) [24]. This results in a dielectric constant almost 2.5 times higher than NiO. Moreover, the critical strain at which the EuO lattice becomes unstable is considerably lower than that for NiO bulk, as it was calculated in case of BaO [15].

EuO belongs to the group of rocksalt binary oxides (space group \(Fm\overline{3}m\)) with a lattice constant of 5.144 Å and a bang gap of \(~ 1.12\) eV [25]. It is the only ferromagnetic binary oxide with rocksalt structure (\(T_C = 69\) K) [26], having a very large local moment on each Eu\(^{2+}\) ion from a half filled 4f band producing a saturation magnetization of \(7 \mu_B\) [26]. The effect of strain on the electronic properties of EuO has been studied in both theory and experiment [27,28]. Ingle and Elfimov [27] showed that using epitaxial strain the curie temperature of EuO increases significantly which was experimentally confirmed by Melville et al. [25]. Axe obtained the dielectric permittivity of around 24 for EuO crystal using Infrared reflectivity [23]. By this time, there is no experimentally study on the effect of strain on the dielectric properties of EuO thin film. Here, we grow the high quality strained EuO thin films via pulsed laser deposition technique on LaAlO\(_3\) substrates and by fabrication of interdigitated electrodes the dielectric features of EuO is studied as a function of strain in a range of temperature from 5 to 200 K.

**Experiments**

**Substrate Preparations**

LaAlO\(_3\) (001) (LAO) single crystals (Crystech) were used as substrates to grow EuO thin films in this work. The relatively low dielectric permittivity of LAO (~ 23) reduces the electric filed penetration in the substrate which results is a more precise measurement of the in-plane dielectric features of thin films through interdigitated electrodes. To remove all possible contaminations from the top surface, a 10-minute ultrasonically cleaning in acetone and methanol was carried out on each substrate. After an ultrasonic soaking in deionized water for 5 minutes followed by a 30-second etching process in the dilute HCl (pH~4.5) to produce a surface that consists of single terminated AlO\(_2\), the annealing treatment at 1000 °C in the air for 2.5 hours was done to obtain atomically smooth surfaces as was already confirmed by Biswas et al. [29].

**Film deposition**

Europium metal pellet (Alfa Aesar, 99.9%) was used as a target to deposit EuO thin films. To ablate the target surface the laser beam produced by a KrF pulsed laser with the wavelength of 248 nm (operating at 10 Hz) was focused through an optical lens on the target, generating an energy fluence of \(~ 2 \) J/cm\(^2\). To obtain a pure EuO phase, the substrate was placed at 50 cm right above the target and its temperature was set at 350 °C during the growth [30]. The chamber was pumped to reach the vacuum of \(10^{-8}\) mbar and all films were deposited under the vacuum condition. All deposited samples were
capped by a 2-nm MgO layer under the same condition. The cooling process was done in vacuum with the rate of 10 °C/min to the room temperature.

Structural Characterization

The phase analysis and structural evaluation of the deposited materials were investigated by X-Ray diffraction machine (XRD) operating at 40 kV 200 mA using a copper source as the x-ray generator. To study the structural features in more detail, theta rocking was done around each detected Bragg peak in XRD spectra. X-ray reflectivity (XRR) was used to determine the film thickness and investigate the quality of interfaces. The surface morphology of substrates and films was studied by Atomic Force Microscopy (AFM) in non-contact mode.

Electronic Measurements

Since the fabrication of a simple in-plane capacitor is not an efficient way to measure the electronic properties of a relatively low dielectric permittivity thin film (EuO), we made interdigitated capacitors (IDE) with enough number of fingers (40 fingers) and small gap between two sides (10 µm) which enable us to investigate the dielectric properties of EuO thin film on LAO (low dielectric permittivity material) substrate. To do so, we used commercial conductive polymer layer (aquaSAVE) on the PMMA coated films to avoid accumulation of electrons during electron beam lithography on the insulating film surface. After the patterning process, we gently removed the conductive layer with DI water. Then a Ti (5 nm) / Au (35 nm) layer was deposited on the pre-made electrode pattern by electron beam evaporator. (See Fig. 1).

Fig. 1. (a) A schematic and, (b) a real image of the interdigitated electrode on EuO films.

The dielectric properties of interdigitated capacitors were measured with a Precision LCR meter (Agilent E4980A) in two different frequencies, 1 kHz and 1 MHz, in the range of temperature from 5 to 200 K. The temperature was increased using a physical properties measurement system by the rate of 2 K/min during the measurement.
Result and Discussion

XRD spectrum of the film grown at 300 °C consists of two different phases (EuO and Eu₂O₃) (see fig. 2). To obtain a single-phase EuO thin film the growth temperature was increased up to 350 °C. Growing a pure EuO film is possible in higher temperatures but to stop the thermal driven strain relaxation processes during the growth, the minimum temperature at which a single-phase EuO oxide is achievable, was selected as the optimum growth temperature [30]. In this work 350 °C was appeared to be the proper temperature to grow strained EuO thin film on LAO (001) substrates.

![XRD pattern of the deposited thin films on LaAlO₃ substrates at different temperatures.](image)

Figure 3 (a) shows the effect of thickness on the XRD pattern of EuO thin films. Increasing thickness is accompanied by the relaxation of the strained film as a 20-nm EuO film grown at 350 °C shows the out-of-plane lattice parameters almost close to the bulk one while 2.8% compression of the out-of plane lattice constant was detected for the 10-nm film which could be due to the in-plane tensile strain induced by the lattice mismatch between LAO and EuO. The theoretical lattice mismatch is about 4%, so the relaxation processes start at the initial stages of growth and a partially relaxed film is obtained after the deposition of almost 20 unit cells (~ 10 nm). The large theoretical lattice mismatch between EuO and LAO causes that the relaxation process starts soon after deposition as the critical thickness for the total relaxation ($h_c$) and theoretical mismatch ($f_{th}$) are inversely proportional [31].

$$h_c \propto \frac{1}{f_{th}} \quad (1)$$

where the theoretical lattice mismatch is
where $a_s$ and $a_0$ are the theoretical lattice parameters of the substrate and film, respectively.

$$f_{th} = \frac{a_s - a_0}{a_0}$$  \(2\)

**Fig. 3.** (a) XRD pattern of the EuO thin films with different thicknesses, (b) XRR spectrum and (c) theta rocking curve around (002) Brag peak of the EuO film.

The X-ray reflectivity pattern of the 20-nm EuO film shows clear fringes (fig. 3(b)), which reveals the high quality interface between film and substrate and also film surface. The latter was confirmed by AFM (see fig. 4). AFM scan revealed that the surface roughness does not exceed 1 nm which is almost in the order of the EuO lattice parameter (~ 5.14 Å). The theta rocking around the 002-EuO peak uncovers more information on the crystalline features of the grown films. Figure 3(c) shows that the rocking curve consist of two different components. A broad component which is due to the mosaic structured area in the film and a narrow component which shows a long range atomically ordered area[32–34]. The mosaic-structured area is a typical feature of the vacuum grown films as there is no decelerating force to reduce the kinetic energy of the ablated particles resulting in defective structured films. Moreover, the large lattice mismatch between film and substrate (~ 4%) also plays an important role in the crystalline quality of the deposited material. Setting the growth parameters, we obtained a long-range atomically ordered film with a small fraction of mosaicity to decrease the presence of any possible charges created by mosaic defects in EuO structure which consequently affects the dielectric properties of the grown samples.
The temperature dependence of the dielectric properties of interdigitated capacitor of europium monoxides grown on LAO substrates is shown in figure 5. We measured the capacitance by applying a 2V-AC voltage, across the 10µm gap, at two different frequencies, 1 kHz and 1 MHz, from 5 to 200 K. The interdigitated capacitors show the capacitance almost constant up to 100 K while above this range a sharp increase was observed which probably indicates the activation of space-charge polarization mechanism, because both electronic and ionic mechanisms of polarization which are available in rocksalt binary oxides, are not that much sensitive to the temperature [35]. Increasing frequency of the applied voltage decreases the high temperature capacitance while the low temperature capacitance (below 100 K) remains constant. The strong dependence of the capacitance to the frequency and temperature above 100 K implies the role of space-charge polarization in the dielectric properties of EuO interdigitated capacitors. On the other side, below 100 K the measured capacitance is independence of the applied frequency and temperature as well, which indicates the role of electronic and ionic polarization in the dielectric permittivity of EuO film.
The capacitance of EuO interdigitated capacitor measured at different frequencies.

The loss tangent of both samples show almost the same behavior under various range of temperature from 5 to 200 K. (see figure 6).

Figure 7 shows the effect of strain on the measured capacitance of interdigitated capacitors. The film under 3% strain shows the capacitance almost 50% higher than that of the relaxed one, which implies the effect of in-plane tensile strain on the dielectric
permittivity of EuO. Increasing the frequency of the measurement to 1 MHz does not have any considerable effect on the dielectric features of these two samples.

Farnell et al. [36] used a finite-difference program to evaluate the capacitance of the periodic interdigitated electrode structure (eq. 3)

$$\epsilon_f = \frac{\left(\frac{C}{K_p} - 1 - \epsilon_s\right)}{1 - \exp\left(-\frac{4.6h}{l}\right)} + \epsilon_s$$

Where $C$ is the measured capacitance per finger length, $h$ is the film thickness, $\epsilon_s$ and $\epsilon_f$ are the dielectric constants of substrate and film, respectively, $l$ is the electrode period and $K_p$ is fitted by a fifth-order polynomial function modified by Kidner et al. [37],

$$K_p = 137.79 \left(\frac{w}{l}\right)^5 - 320.72 \left(\frac{w}{l}\right)^4 + 288.22 \left(\frac{w}{l}\right)^3 - 120.47 \left(\frac{w}{l}\right)^2 + 28.55 \left(\frac{w}{l}\right)$$

Where $w$ stands for the electrode width.

Applying these equations to our interdigitated pattern shows that 50% increase of the capacitance corresponds to a nearly 9 times enhancement of the dielectric permittivity of the EuO film as a function of strain which could be due to strongly softening of the in-plane TO phonon mode due to the lattice elongation in $x$ and $y$ direction.

Bousquet et al.[15] using first principles density functional calculations predicted the enhancement of the dielectric permittivity in the EuO under epitaxial tensile strain. According to their calculation under in-plane biaxial tensile strain the triple degenerate cubic TO phonon mode with $F_{1u}$ symmetry at zone center ($\Gamma$ point) splits to a single non-degenerate $A_{2u}$ mode polarized along the [001] axis, and a twofold degenerate $E_u$ mode.
polarized along [100] or [010] axis results in a phase transition to the tetragonal structure (space group I4/mmm). The increase of in-plane tensile strain decreases the frequency of twofold degenerate Eu phonon mode results in an increase in the in-plane dielectric permittivity of EuO thin film. According to the Bog G Kim [14], the tensile strain decreases the electron overlap between anion and cation, results in a weak bonding between them and subsequently a softening of the transverse optical phonon mode which is a basic component in the determination of dielectric behavior of a rocksalt binary oxide according to the Lyddane–Sachs–Teller relation [38].

\[
\frac{\varepsilon(0)}{\varepsilon(\infty)} = \prod_j \frac{\omega_{Lj}^2}{\omega_{Tj}^2}
\]

where \(\omega_L\) and \(\omega_T\) are the frequencies of the longitudinal and transverse optical phonon modes, respectively, \(\varepsilon(0)\) is the low-frequency dielectric permittivity and \(\varepsilon(\infty)\) is the high-frequency limit for electronic dielectric permittivity. Decreasing the \(\omega_T\) due to the tensile strain is accompanied by enhancement of low frequency dielectric constant.
Conclusion

Dielectric properties of the strained PLD grown EuO thin films have been studied as a function of temperature. The XRD and AFM results showed that the atomically long-range ordered pure EuO films are achievable using pulsed laser deposition technique. A nearly 3% out-of-plane lattice compression in the 10-nm EuO film on LAO substrate was observed which could be due to the lattice mismatch of the film and substrate. The in-plane dielectric features of the strained film shows a dielectric constant almost 9 times higher than that of the relaxed film as had been predicted based on the investigation of the lattice dynamics of rocksalt binary compounds. This result implies the substantial role of tensile strain on the softening of TO phonon mode of EuO, which is a basic element of the dielectric properties of rocksalt binary oxides based on the Lyddane–Sachs–Teller relation.

Acknowledgments

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